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# MAC15A6FP, MAC15A8FP, MAC15A10FP

Preferred Device




**ON Semiconductor**

<http://onsemi.com>


## Triacs

### Silicon Bidirectional Thyristors

Designed primarily for full-wave ac control applications, such as solid-state relays, motor controls, heating controls and power supplies; or wherever full-wave silicon gate controlled solid-state devices are needed. Triac type thyristors switch from a blocking to a conducting state for either polarity of applied main terminal voltage with positive or negative gate triggering.


- Blocking Voltage to 800 Volts
- All Diffused and Glass Passivated Junctions for Greater Parameter Uniformity and Stability
- Small, Rugged, Thermowatt Construction for Low Thermal Resistance, High Heat Dissipation and Durability
- Gate Triggering Guaranteed in Four Modes
-  Indicates UL Registered — File #E69369
- Device Marking: Logo, Device Type, e.g., MAC15A6FP, Date Code

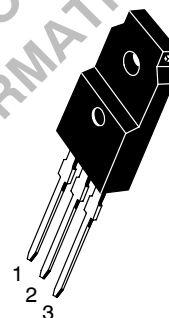
#### MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Peak Repetitive Off-State Voltage <sup>(1)</sup> (T <sub>J</sub> = -40 to +125°C, Sine Wave 50 to 60 Hz, Gate Open)	V <sub>DRM</sub> , V <sub>RRM</sub>	400 600 800	Volts
On-State RMS Current (T <sub>C</sub> = +80°C) <sup>(2)</sup> Full Cycle Sine Wave 50 to 60 Hz (T <sub>C</sub> = +95°C)	I <sub>T(RMS)</sub>	15 12	Amps
Peak Nonrepetitive Surge Current (One Full Cycle Sine Wave, 60 Hz, T <sub>C</sub> = +80°C) Preceded and followed by rated current	I <sub>TSM</sub>	150	Amps
Circuit Fusing (t = 8.3 ms)	I <sup>2</sup> t	93	A <sup>2</sup> s
Peak Gate Power (T <sub>C</sub> = +80°C, Pulse Width = 2.0 μs)	P <sub>GM</sub>	20	Watts
Average Gate Power (T <sub>C</sub> = +80°C, t = 8.3 ms)	P <sub>G(AV)</sub>	0.5	Watt
Peak Gate Current (Pulse Width ≤ 1.0 μsec; T <sub>C</sub> = 80°C)	I <sub>GM</sub>	2.0	Amps
Peak Gate Voltage (Pulse Width ≤ 1.0 μsec; T <sub>C</sub> = 80°C)	V <sub>GM</sub>	10	Volts
RMS Isolation Voltage (T <sub>A</sub> = 25°C, Relative Humidity ≤ 20%) 	V <sub>(ISO)</sub>	1500	Volts
Operating Junction Temperature	T <sub>J</sub>	-40 to +125	°C
Storage Temperature Range	T <sub>stg</sub>	-40 to +150	°C

(1) V<sub>DRM</sub> and V<sub>RRM</sub> for all types can be applied on a continuous basis. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

(2) The case temperature reference point for all T<sub>C</sub> measurements is a point on the center lead of the package as close as possible to the plastic body.

**ISOLATED TRIAC **  
**15 AMPERES RMS**  
**400 thru 800 VOLTS**



**ISOLATED TO-220 Full Pack**  
**CASE 221C**  
**STYLE 3**

PIN ASSIGNMENT	
1	Main Terminal 1
2	Main Terminal 2
3	Gate

#### ORDERING INFORMATION

Device	Package	Shipping
MAC15A6FP	ISOLATED TO220FP	500/Box
MAC15A8FP	ISOLATED TO220FP	500/Box
MAC15A10FP	ISOLATED TO220FP	500/Box

Preferred devices are recommended choices for future use and best overall value.

# MAC15A6FP, MAC15A8FP, MAC15A10FP

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	2.0	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Case to Sink	$R_{\theta CS}$	2.2 (typ)	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	60	$^{\circ}\text{C}/\text{W}$
Maximum Lead Temperature for Soldering Purposes 1/8" from Case for 10 Seconds	$T_L$	260	$^{\circ}\text{C}$

## ELECTRICAL CHARACTERISTICS ( $T_C = 25^{\circ}\text{C}$ unless otherwise noted; Electricals apply in both directions)

Characteristic	Symbol	Min	Typ	Max	Unit
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## OFF CHARACTERISTICS

Peak Repetitive Blocking Current ( $V_D = \text{Rated } V_{DRM}, V_{RRM}; \text{ Gate Open}$ )	$T_J = 25^{\circ}\text{C}$ $T_J = 125^{\circ}\text{C}$	$I_{DRM}$ $I_{RRM}$	— —	— —	10 2.0	$\mu\text{A}$ $\text{mA}$
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## ON CHARACTERISTICS

Peak On-State Voltage <sup>(1)</sup> ( $I_{TM} = \pm 21 \text{ A Peak}$ )	$V_{TM}$	—	1.3	1.6	Volts
Gate Trigger Current (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	$I_{GT}$	— — — —	— — — —	50 50 50 75	$\text{mA}$
Gate Trigger Voltage (Continuous dc) (Main Terminal Voltage = 12 Vdc, $R_L = 100 \text{ Ohms}$ ) MT2(+), G(+) MT2(+), G(-) MT2(-), G(-) MT2(-), G(+)	$V_{GT}$	— — — —	0.9 0.9 1.1 1.4	2.0 2.0 2.0 2.5	Volts
Gate Non-Trigger Voltage (Main Terminal Voltage = Rated $V_{DRM}$ , $R_L = 100 \Omega$ , $T_J = +110^{\circ}\text{C}$ ) All 4 Quadrants	$V_{GD}$	0.2	—	—	Volts
Holding Current (Main Terminal Voltage = 12 Vdc, Gate Open, Initiating Current = $\pm 200 \text{ mA}$ )	$I_H$	—	6.0	40	$\text{mA}$
Turn-On Time ( $V_D = \text{Rated } V_{DRM}$ , $I_{TM} = 17 \text{ A}$ , $I_{GT} = 120 \text{ mA}$ , Rise Time = $0.1 \mu\text{s}$ , Pulse Width = $2 \mu\text{s}$ )	$t_{gt}$	—	1.5	—	$\mu\text{s}$

## DYNAMIC CHARACTERISTICS

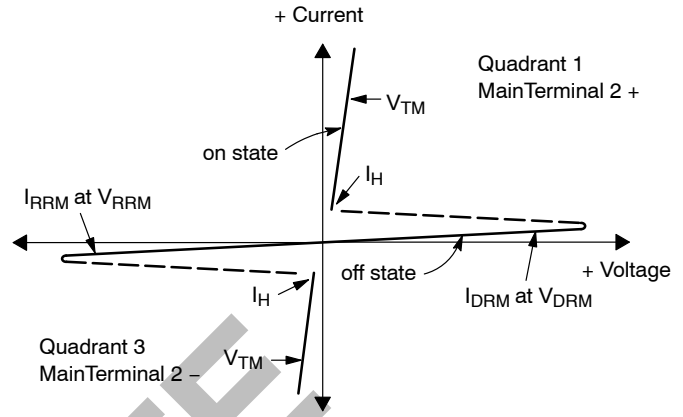
Critical Rate of Rise of Commutation Voltage ( $V_D = \text{Rated } V_{DRM}, V_{RRM}, I_{TM} = 21 \text{ A}$ , Commutating $di/dt = 7.6 \text{ A/ms}$ , Gate Unenergized, $T_C = 80^{\circ}\text{C}$ )	$dv/dt(c)$	—	5.0	—	$\text{V}/\mu\text{s}$
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(1) Pulse Test: Pulse Width  $\leq 2.0 \text{ ms}$ , Duty Cycle  $\leq 2\%$ .

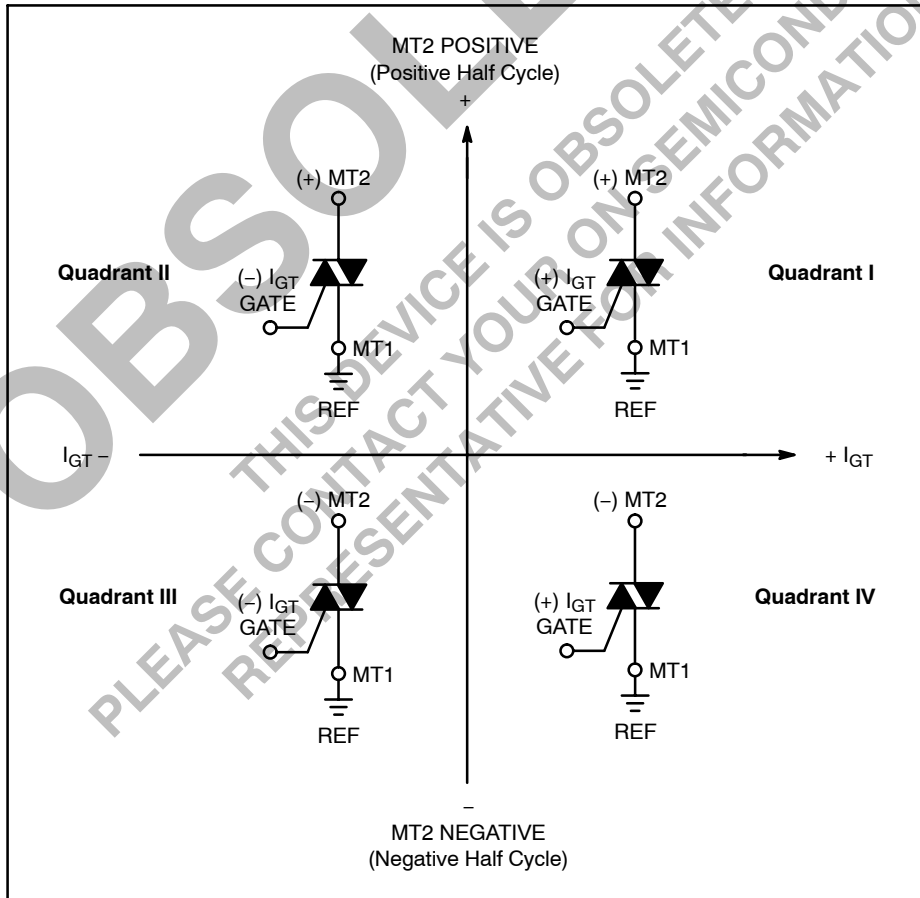
# MAC15A6FP, MAC15A8FP, MAC15A10FP

## Voltage Current Characteristic of Triacs (Bidirectional Device)

Symbol	Parameter
$V_{DRM}$	Peak Repetitive Forward Off State Voltage
$I_{DRM}$	Peak Forward Blocking Current
$V_{RRM}$	Peak Repetitive Reverse Off State Voltage
$I_{RRM}$	Peak Reverse Blocking Current
$V_{TM}$	Maximum On State Voltage
$I_H$	Holding Current



### Quadrant Definitions for a Triac



All polarities are referenced to MT1.

With in-phase signals (using standard AC lines) quadrants I and III are used.

# MAC15A6FP, MAC15A8FP, MAC15A10FP

## TYPICAL CHARACTERISTICS

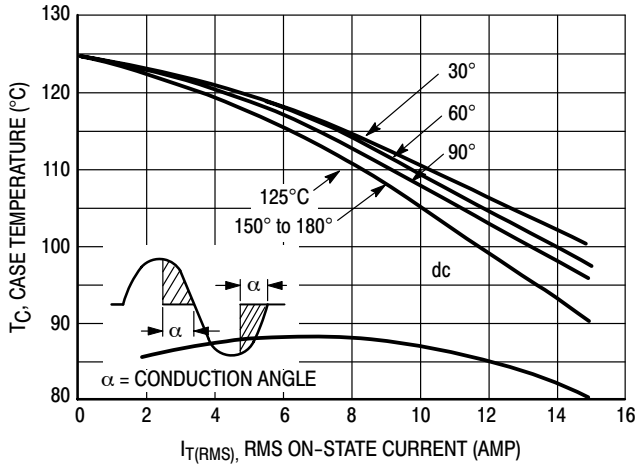


Figure 1. RMS Current Derating

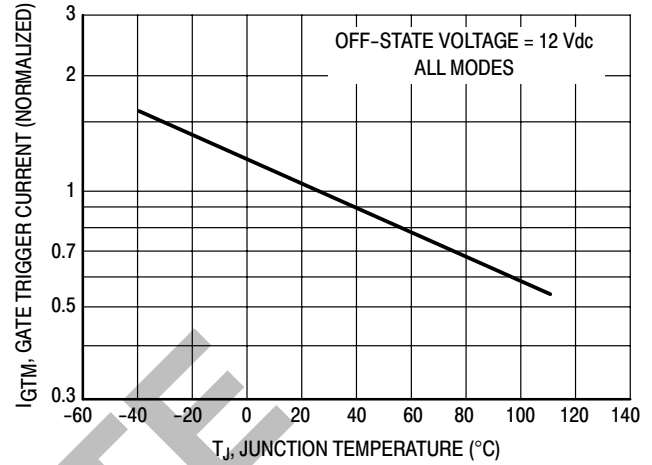


Figure 4. Typical Gate Trigger Current

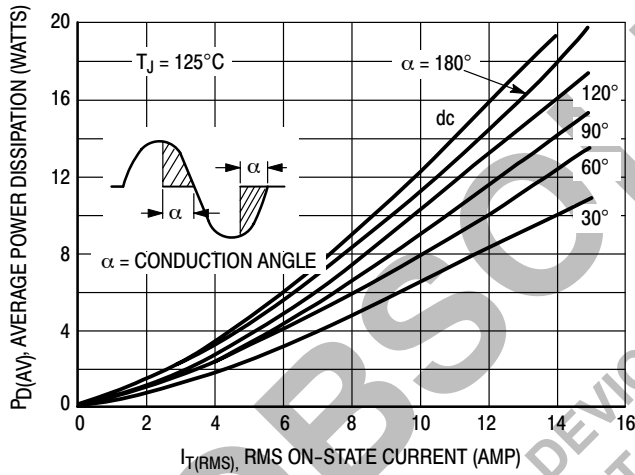


Figure 2. On-State Power Dissipation

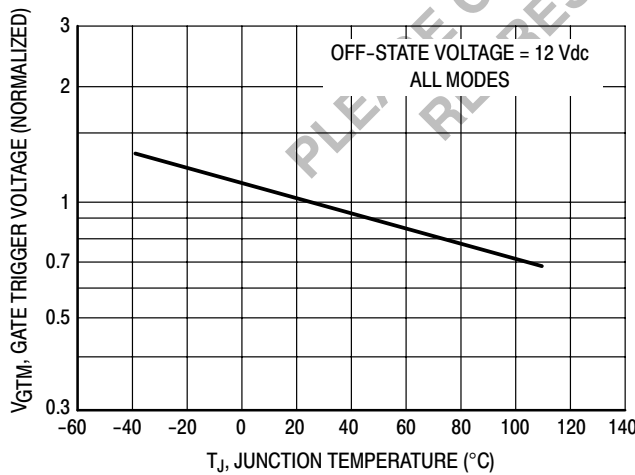


Figure 3. Typical Gate Trigger Voltage

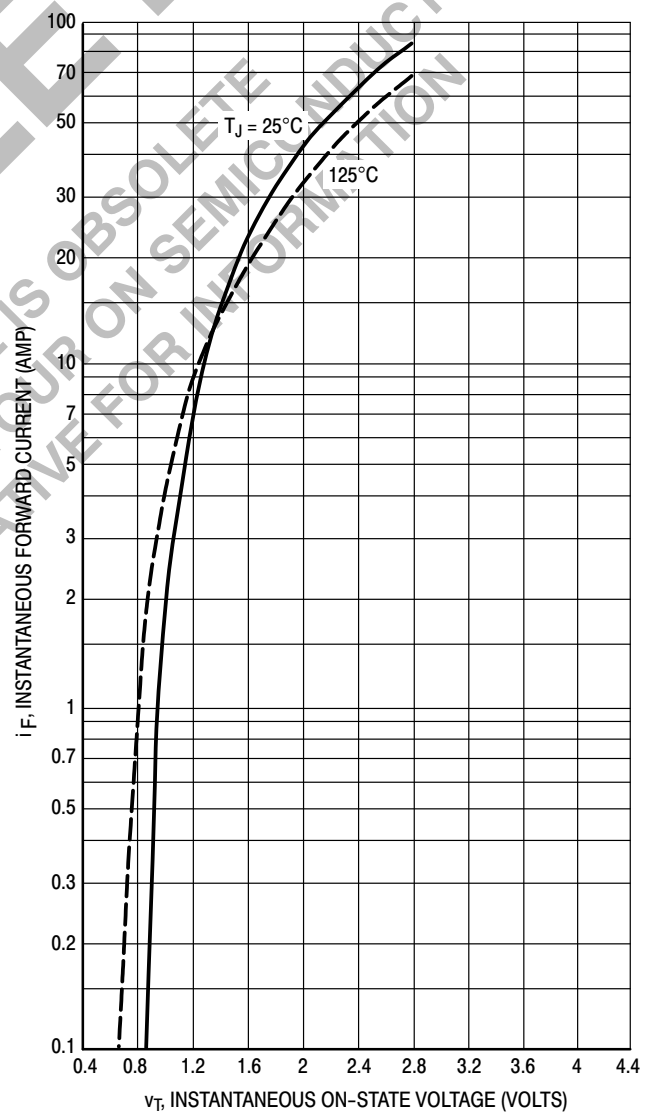


Figure 5. Maximum On-State Characteristics

# MAC15A6FP, MAC15A8FP, MAC15A10FP

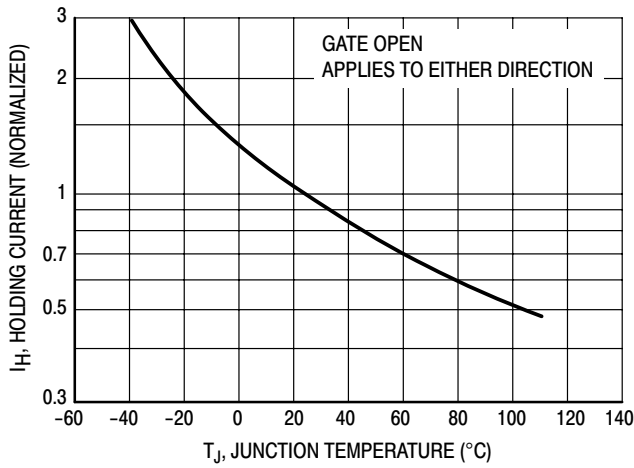


Figure 6. Typical Holding Current

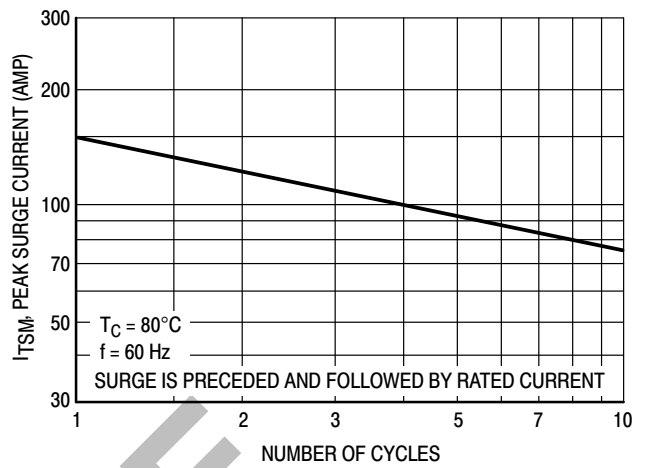


Figure 7. Maximum Nonrepetitive Surge Current

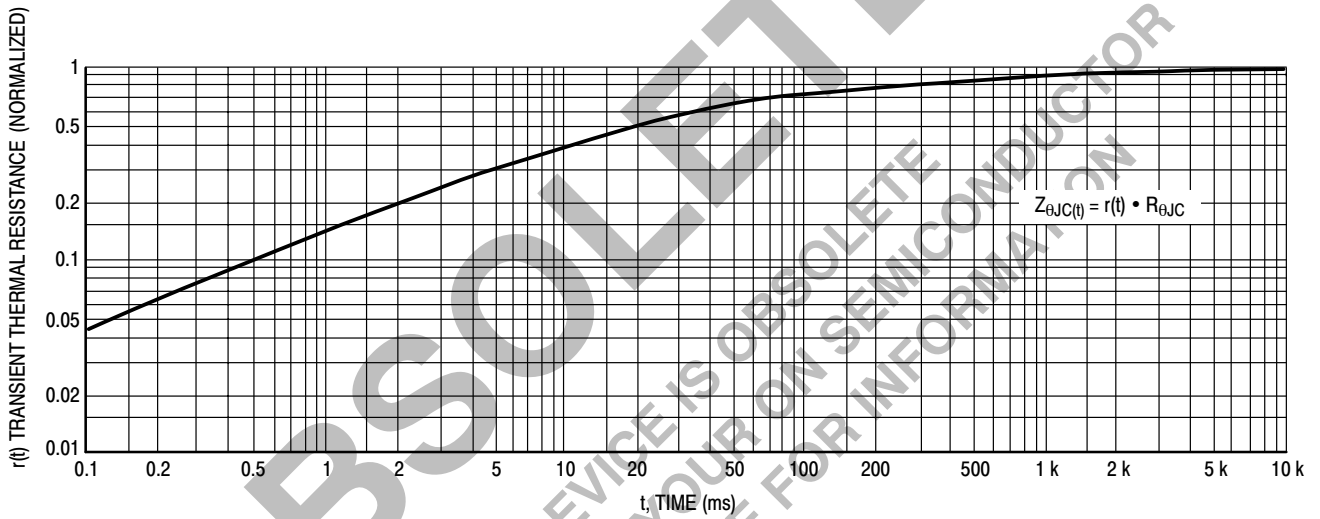
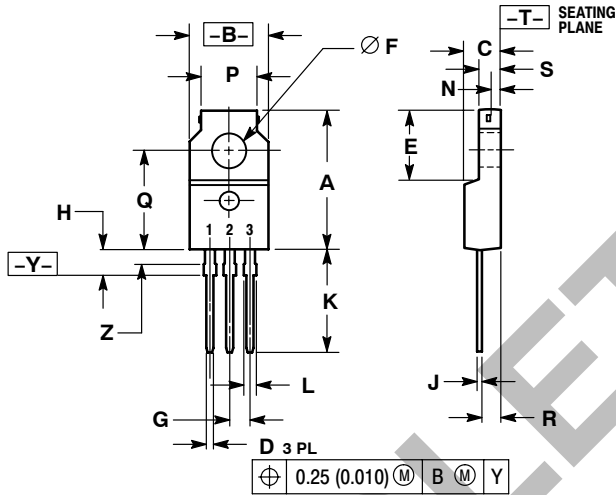


Figure 8. Thermal Response

# MAC15A6FP, MAC15A8FP, MAC15A10FP

## PACKAGE DIMENSIONS


### ISOLATED TO-220 Full Pack CASE 221C-02 ISSUE C



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
  2. CONTROLLING DIMENSION: INCH.
  3. LEAD DIMENSIONS UNCONTROLLED WITHIN DIMENSION Z.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.680	0.700	17.28	17.78
B	0.388	0.408	9.86	10.36
C	0.175	0.195	4.45	4.95
D	0.025	0.040	0.64	1.01
E	0.340	0.355	8.64	9.01
F	0.140	0.150	3.56	3.81
G	0.100 BSC		2.54 BSC	
H	0.110	0.155	2.80	3.93
J	0.018	0.028	0.46	0.71
K	0.500	0.550	12.70	13.97
L	0.045	0.070	1.15	1.77
N	0.049	---	1.25	---
P	0.270	0.290	6.86	7.36
Q	0.480	0.500	12.20	12.70
R	0.090	0.120	2.29	3.04
S	0.105	0.115	2.67	2.92
Z	0.070	0.090	1.78	2.28

- STYLE 3:  
PIN 1: MT 1  
2: MT 2  
3: GATE

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